TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

# 2 S C 4 2 0 9

DRIVER STAGE AMPLIFIER APPLICATIONS

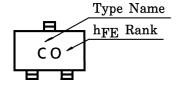
**VOLTAGE AMPLIFIER APPLICATIONS** 

• Complementary to 2SA1620

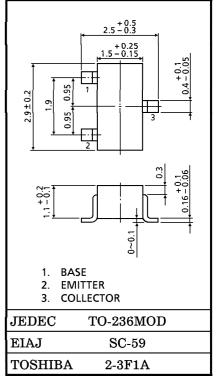
### MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$v_{CBO}$	80	V
Collector-Emitter Voltage	$v_{CEO}$	80	V
Emitter-Base Voltage	$V_{ m EBO}$	5	V
Collector Current	$I_{\mathbf{C}}$	300	mA
Base Current	$I_{\mathrm{B}}$	60	mA
Collector Power Dissipation	$P_{\mathbf{C}}$	200	mW
Junction Temperature	$T_{j}$	150	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~150	°C

#### **MARKING**



Unit in mm



Weight: 0.012g

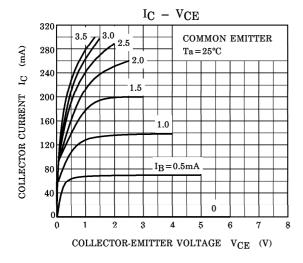
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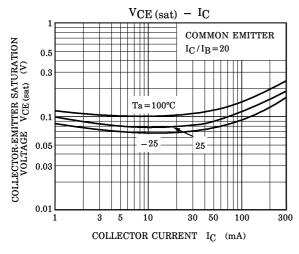
## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

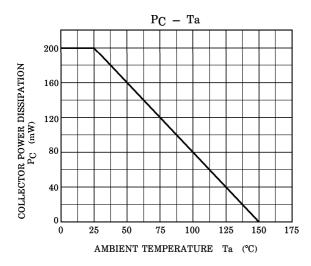
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 50V, I_{E} = 0$	_	_	0.1	$\mu$ A
Emitter Cut-off Current	$I_{ m EBO}$	$V_{EB}=5V, I_{C}=0$	_	_	0.1	$\mu$ <b>A</b>
Collector-Emitter Breakdown Voltage	V (BR ) CEO	$I_{\rm C}$ =5mA, $I_{\rm B}$ =0	80	_	_	V
DC Current Gain	hFE (1) (Note)	$V_{ m CE}$ =2V, $I_{ m C}$ =50mA	70	_	240	
	h <sub>FE (2)</sub>	$V_{CE}=2V$ , $I_{C}=200mA$	40	_	_	
Collector-Emitter Saturation Voltage	V <sub>CE</sub> (sat)	$I_{\rm C} = 200  {\rm mA}, \ I_{\rm B} = 10  {\rm mA}$	_	_	0.5	V
Base-Emitter VOltage	$ m V_{BE}$	$V_{CE}=2V, I_{C}=5mA$	0.55	_	0.8	V
Transition Frequency	${f f_T}$	$V_{CE} = 10V, I_C = 10mA$	_	100	_	MHz
Collector Output Capacitance	$C_{ m ob}$	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$	_	10	_	pF

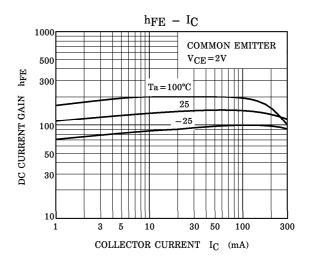
(Note):  $h_{FE(1)}$  Classification  $O: 70\sim140, Y: 120\sim240$ 

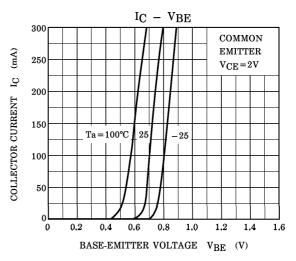
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